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High Power LED Series Chip on Board

LC006B



High efficacy COB LED package, well-suited for use in spotlight applications



- Chip on Board (COB) solution makes it easy to design in
- Simple assembly reduces manufacturing cost
- Low thermal resistance
- InGaN/GaN MQW LED with long time reliability
- Completed 6,000 hours of LM-80 Testing
- ENEC certified: Integral LED Module

Applications

- Spotlight / Downlight
- LED Retrofit Bulbs
- Outdoor Illumination











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1. Characteristics

a) Absolute Maximum Rating

Item	Symbol	Rating	Unit	Condition
Ambient / Operating Temperature	Ta	-40 ~ +105	°C	-
Storage Temperature	T _{stg}	-40 ~ +120	°C	_
LED Junction Temperature	T _j	140	°C	-
Case Temperature	Tc	105	°C	*Note
Forward Current	l _F	320	mA	_
Power Dissipation	P _D	12.2	W	-
ESD (HBM)	_	±2	kV	_
ESD (MM)	_	±0.5	kV	-

b) Electro-optical Characteristics (I_F = 180 mA, T_c = 25 °C)

ltem	Unit	Rank	Min.	Тур.	Max.
Forward Voltage (V _F)	V	YH	32.5	35.5	38.5
		3	70	-	-
Calau Dandavian Indau (D.)		5	80	_	-
Color Rendering Index (R₃)	-	7	90	_	_
		8	95		
Thermal Resistance (junction to chip point)	°C/W		_	2.4	_
Beam Angle	0		_	115	_
Working Voltage for Insulation	V				50
Nominal Power	W			6.4	
Eye Protection		Risk 1	_		-

Notes:

- 1) The COB is tested in pulsed condition at rated test current (10 ms pulse width) and rated temperature ($T_j = T_c = T_a = 25$ °C)
- 2) Samsung maintains measurement tolerance of: forward voltage = ± 5 %, CRI = ± 1
- 3) Max Tc=105°C (at max current) is for ENEC condition. Refer to the derating curve, '3. Typical Characteristics Graph' designed within the range.



c) Luminous Flux Characteristics (I_F = 180 mA, T_c = 25 °C)

CRI (R _a)	Nominal	Flux	Flux	Sorting ¹⁾ @ T	Sorting ¹⁾ @ $T_c = 25$ °C (lm)		Calculated Flux ²⁾ @ $T_c = 85$ °C (lm)	
Min.	CCT (K)	Rank	Bin	Min.	Max.	Min.	Max.	
	2000	OF	G1	796	905	716	814	
	3000	GE	G2	905	1013	814	912	
70	4000	05	G1	836	950	752	855	
70	4000	GE	G2	950	1064	855	957	
	5000	05	G1	844	959	759	863	
	5000	GE	G2	959	1074	863	967	
			E1	724	779	659	709	
	2700	ED	E2	779	833	709	758	
			E3	833	888	758	808	
			E1	771	829	701	754	
	3000	ED	E2	829	887	754	807	
			E3	887	945	807	860	
			E1	794	853	722	777	
	3500	ED	E2	853	913	777	831	
			E3	913	973	831	885	
80			E1	817	878	743	799	
	4000	ED	E2	878	940	799	855	
			E3	940	1001	855	911	
			E1	825	887	750	807	
	5000	ED	E2	887	949	807	863	
			E3	949	1011	863	920	
	5700		E1	825	887	750	807	
		ED	E2	887	949	807	863	
			E3	949	1011	863	920	
			C1	642	698	585	636	
	2700	CF	C2	698	754	636	686	
			C3	754	810	686	737	
			C1	656	713	597	648	
	3000	CF	C2	713	770	648	700	
			C3	770	827	700	752	
90			C1	675	734	615	668	
	3500	CF	C2	734	793	668	721	
			C3	793	851	721	775	
			C1	695	755	632	687	
	4000	CF	C2	755	816	687	742	
			C3	816	876	742	797	
		0.5	C1	566	629	515	572	
	2700	CC	C2	629	691	572	629	
		_	C1	583	648	531	590	
95	3000	CC	C2	648	713	590	649	
		_	C1	601	667	547	607	
	3500	CC	C2	667	734	607	668	

Notes:

- 1) The COB is tested in pulsed condition at rated test current (10 ms pulse width) and rated temperature ($T_i = T_c = T_a = 25$ °C)
- 2) Calculated flux values are for reference only
- 3) Samsung maintains measurement tolerance of: luminous flux = ± 7 %, CRI = ± 1



2. Product Code Information

1	2	3	4	5	6	7	8	9	10	11	12	13	14	15	16	17	18
S	Р	н	C	w	1	н	D	N	8	2	5	Υ	н	R	т	E	D

Digit	PKG Information	Code				Specificat	tion
1 2 3	Samsung Package High Power	SPH					
4 5	Color	ww	Warm White	(T/U/	V/W Rank	(s)	
4 5	Color	cw	Cool White	(Q/R	Ranks)		
6	Product Version	1					
7 8	Form Factor	HD	COB				
9	Lens Type	N	No lens				
10	Internal Code	8	LC006				
11	Chip Type	2					
		3	Min. 70				
12	CRI & Sorting Temperature	5	Min. 80	5 °C			
12	Ortik Corting Temperature	7	Min. 90	0 0			
		8	Min 95				
13 14	Forward Voltage (V)	YH	32.5~38.5				
		w	2700 K		WA,WB	(MacAdam Ellipse)	
		V	3000 K		VA, VB	(MacAdam Ellipse)	VW, VX, VY, VZ (ANSI bin)
15	CCT (K)	U		Bin	UA, UB	(MacAdam Ellipse)	
	001 (1)	Т	4000 K	Code:	TA, TB	(MacAdam Ellipse)	TW, TX, TY, TZ (ANSI bin)
		R	5000 K		RA	(MacAdam Ellipse)	RW, RX, RY, RZ (ANSI bin)
		Q	5700 K				QW, QX, QY, QZ (ANSI bin)
		2	MacAdam 2-	-step			
16	MacAdam / ANSI	3	MacAdam 3-	step			
		Т	ANSI bin				
		GE			G1, G2	(70 CRI)	
17 18	Luminous Flux	ED		Bin	E1, E2, E3	3 (80 CRI)	
		CF		Code:	C2, C3, E	1 (90 CRI)	
		СС			C1, C2 (9	5 CRI)	



a) Binning Structure (I_F = 180 mA, T_c = 25 °C)

CRI (R₃) Min.	Nominal CCT (K)	Product Code	V _F Rank	Color Rank	Chrom. Bin	Flux Rank	Flux Bin	Flux Range (Φ _v , lm)
	3000	SPHWW1HDN823YHVTGE	ΥH	VT	VW, VX	GE	G1	796 ~ 905
	0000	OI TIWW TIIDNOZOTTIV I GE		V I	VY, VZ	GL	G2	905 ~ 1013
70	4000	SPHWW1HDN823YHTTGE	ΥH	TT	TW, TX	GE	G1	836 ~ 950
. 0		or more than the second of the			TY, TZ	GL.	G2	950 ~ 1064
	5000	SPHCW1HDN823YHRTGE	ΥH	RT	RW, RX	GE	G1	844 ~ 959
		OF HOW HIDNOZOTHIN GE			RY, RZ	GL.	G2	959 ~ 1074
							E1	724 ~ 779
		SPHWW1HDN825YHW2ED	YH	W2	WB	ED	E2	779 ~ 833
	2700						E3	833 ~ 888
	2700						E1	724 ~ 779
		SPHWW1HDN825YHW3ED	YH	W3	WA, WB	ED	E2	779 ~ 833
							E3	833 ~ 888
							E1	771 ~ 829
		SPHWW1HDN825YHV2ED	YH	V2	VB	ED	E2	829 ~ 887
	3000						E3	887 ~ 945
	0000						E1	771 ~ 829
		SPHWW1HDN825YHV3ED	YH	V3	VA, VB	ED	E2	829 ~ 887
							E3	887 ~ 945
							E1	794 ~ 853
		SPHWW1HDN825YHU2ED	YH	U2	UB	ED	E2	853 ~ 913
	3500						E3	913 ~ 973
	3300						E1	794 ~ 853
80		SPHWW1HDN825YHU3ED	YH	U3	UA, UB	ED	E2	853 ~ 913
							E3	913 ~ 973
				T2			E1	817 ~ 878
		SPHWW1HDN825YHT2ED	YH		ТВ	ED	E2	878 ~ 940
	4000						E3	940 ~ 1001
	4000						E1	817 ~ 878
		SPHWW1HDN825YHT3ED	ΥH	Т3	TA, TB	ED	E2	878 ~ 940
							E3	940 ~ 1001
							E1	825 ~ 887
		SPHCW1HDN825YHR3ED	YH	R3	RA	ED	E2	887 ~ 949
	F000						E3	949 ~ 1011
	5000						E1	825 ~ 887
		SPHCW1HDN825YHRTED	YH	RT	RW, RX, RY, RZ	ED	E2	887 ~ 949
					111,112		E3	949 ~ 1011
							E1	825 ~ 887
	5700	SPHCW1HDN825YHQTED	ΥH	QT	QW, QX, QY, QZ	ED	E2	887 ~ 949
					Q1, QZ		E3	949 ~ 1011

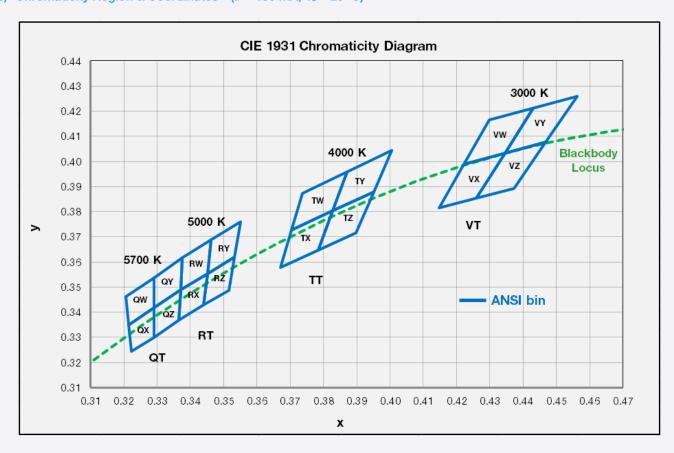


a) Binning Structure (I_F = 180 mA, T_c = 25 °C)

CRI (R₃) Min.	Nominal CCT (K)	Product Code	V _F Rank	Color Rank	Chrom. Bin	Flux Rank	Flux Bin	Flux Range (Φ _v , lm)
							C1	642 ~ 698
		SPHWW1HDN827YHW2CF	ΥH	W2	WB	CF	C2	698 ~ 754
	2700						C3	754 ~ 810
	2700 "						C1	642 ~ 698
		SPHWW1HDN827YHW3CF	ΥH	W3	WA, WB	CF	C2	698 ~ 754
							C3	754 ~ 810
							C1	656 ~ 713
		SPHWW1HDN827YHV2CF	ΥH	V2	VB	CF	C2	713 ~ 770
	3000						C3	770 ~ 827
	3000 "						C1	656 ~ 713
		SPHWW1HDN827YHV3CF	YH	V3	VA, VB	CF	C2	713 ~ 770
90							C3	770 ~ 827
90							C1	675 ~ 734
		SPHWW1HDN827YHU2CF	ΥH	U2	UB	CF	C2	734 ~ 793
	3500						C3	793 ~ 851
	3300 "						C1	675 ~ 734
		SPHWW1HDN827YHU3CF	ΥH	U3	UA, UB	CF	C2	734 ~ 793
							C3	793 ~ 851
	4000	SPHWW1HDN827YHT2CF					C1	695 ~ 755
			ΥH	T2	TB	CF	C2	755 ~ 816
							C3	816 ~ 876
	4000			Т3			C1	695 ~ 755
		SPHWW1HDN827YHT3CF	ΥH		TA, TB	CF	C2	755 ~ 816
							C3	816 ~ 876
		SPHWW1HDN828YHW2CC	ΥH	W2	WB	CC	C1	566 ~ 629
	2700	3PHWW1HDINOZOTHWZGG	IП	VVZ	VVD	00	C2	629 ~ 691
	2700 "	SPHWW1HDN828YHW3CC	ΥH	W3	WA,WB	CC	C1	566 ~ 629
		SPRWW IRDINOZOTRWSCO	тп	VVS	VVA,VVD	00	C2	629 ~ 691
		SPHWW1HDN828YHV2CC	ΥH	V2	VB	CC	C1	583 ~ 648
95	2000	SPHWWINDINOZOTHVZCC	IП	٧∠	VD	CC	C2	648 ~ 713
90	3000	SPHWW1HDN828YHV3CC	ΥH	V3	VA,VB	CC	C1	583 ~ 648
		31° FIVVVV I FIDINOZO I FIVSUU	IΠ	VO	VA,VD	00	C2	648 ~ 713
		CDUMMHUDNIO20VUI 1200	VLI	110	LID	00	C1	601 ~ 667
	3500	SPHWW1HDN828YHU2CC	YH	U2	UB	CC	C2	667 ~ 734
	3300 "	SPHWW1HDN828YHU3CC	ΥH	U3	UA,UB	CC	C1	601 ~ 667
		31 1144 44 11110140201110300	111	00	UA,UB	00	C2	667 ~ 734



b) Chromaticity Region & Coordinates (I_F = 180 mA, T_a = 25 °C)

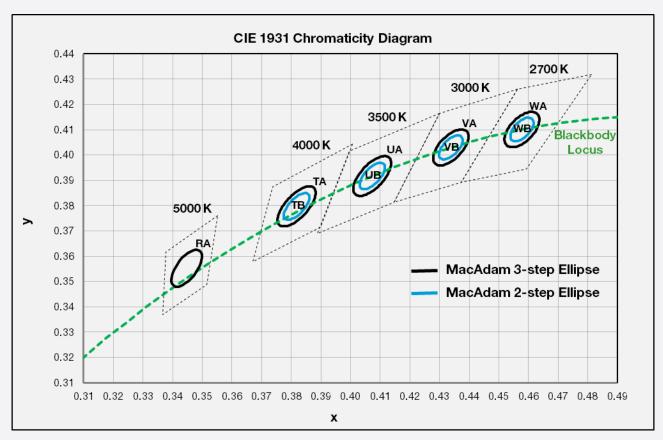


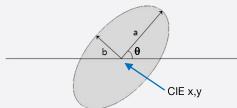
Region	CIE x	CIE y	Region	CIE x	CIE y							
	V rank (3000 K)											
	0.4223	0.399		0.4345	0.4033							
VW	0.4345	0.4033	VY	0.4468	0.4077							
VVV	0.4431	0.4213	VY	0.4562	0.4260							
	0.4299	0.4165		0.4431	0.4213							
	0.4223	0.399		0.4260	0.3854							
\/\	0.4147	0.3814	VZ	0.4373	0.3893							
VX	0.4260	0.3854		0.4468	0.4077							
	0.4345	0.4033		0.4345	0.4033							
		R rank	(5000 K)									
	0.3376	0.3616		0.3463	0.3687							
DW	0.3463	0.3687	D)/	0.3551	0.3760							
RW	0.3451	0.3554	RY	0.3533	0.3620							
	0.3371	0.3490		0.3451	0.3554							
	0.3371	0.3490		0.3451	0.3554							
DV	0.3451	0.3554	DZ	0.3533	0.3620							
RX	0.3440	0.3428	RZ	0.3515	0.3487							
	0.3366	0.3369		0.3440	0.3428							

Region	CIEx	CIE y	Region	CIE x	CIE y
		T rank	(4000 K)		
	0.3736	0.3874		0.3871	0.3959
TW	0.3871	0.3959	TY	0.4006	0.4044
IVV	0.3828	0.3803	11	0.3952	0.388
	0.3703	0.3726		0.3828	0.3803
	0.3703	0.3726	0.3828	0.3803	
TX	0.3828	0.3803	TZ	0.3952	0.388
1.	0.3784	0.3647		0.3898	0.3716
	0.367	0.3578		0.3784	0.3647
		Q rank	(5700 K)		
	0.3207	0.3462		0.3290	0.3538
OW	0.3290	0.3538	QY	0.3376	0.3616
QVV	0.3290	0.3417	QY	0.3371	0.3490
	0.3215	0.3350		0.3290	0.3417
	0.3215	3215 0.3350	0.3290	0.3417	
OV	0.3290	0.3417	07	0.3371	0.3490
QX	0.3290	0.3300	QZ	0.3366	0.3369
	0.3222	0.3243		0.3290	0.3300



b) Chromaticity Region & Coordinates (I_F = 180 mA, T_a = 25 °C)





MacAdam Ellipse (WA, WB)										
Step	CIE x	CIE y			b					
2-step	0.4578	0.4101	53.70	0.0054	0.0028					
3-step	0.4578	0.4101	53.70	0.0081	0.0042					

MacAdam Ellipse (UA, UB)										
Step	CIE x	CIE y			b					
2-step	0.4073	0.3917	54.00	0.0062	0.0028					
3-step	0.4073	0.3917	54.00	0.0093	0.0041					

MacAdam Ellipse (RA)						
Step		b				
3-step	0.3447	0.3553	59.62	0.0082	0.0035	

MacAdam Ellipse (VA, VB)						
Step		b				
2-step	0.4338	0.403	53.22	0.0056	0.0027	
3-step	0.4338	0.4030	53.22	0.0083	0.0041	

MacAdam Ellipse (TA, TB)						
Step	Step CIE x CIE y θ a					
2-step	0.3818	0.3797	53.72	0.0063	0.0027	
3-step	0.3818	0.3797	53.72	0.0094	0.0040	

Note:

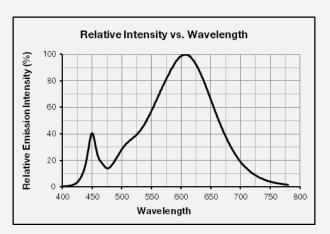
Samsung maintains measurement tolerance of: Cx, $Cy = \pm 0.005$



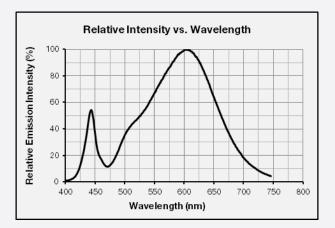
3. Typical Characteristics Graphs

a) Spectrum Distribution ($I_F = 180 \text{ mA}, T_c = 25 \text{ }^{\circ}\text{C}$)

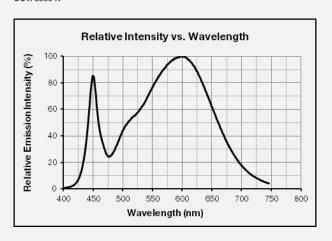
CCT: 2700 K



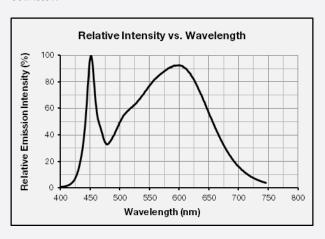
CCT: 3000 K



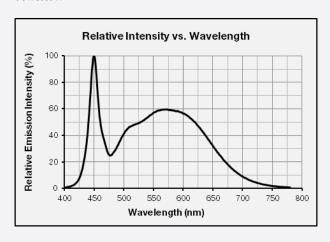
CCT: 3500 K



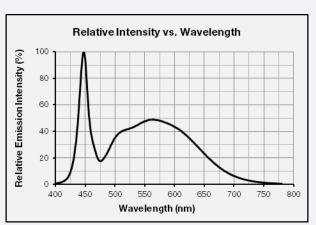
CCT: 4000 K



CCT: 5000 K

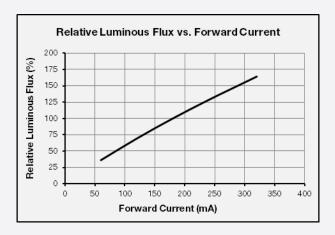


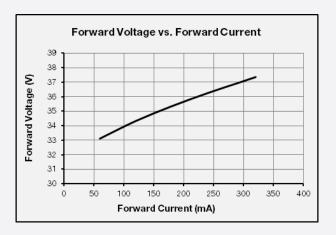
CCT: 5700 K



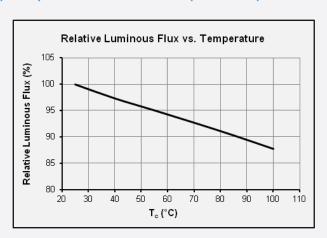


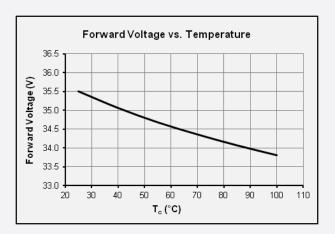
b) Forward Current Characteristics (T_c = 25 °C)





c) Temperature Characteristics (I_F = 180 mA)

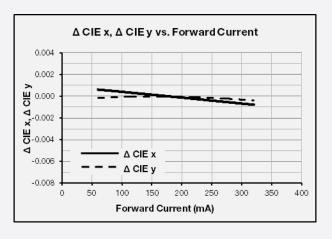


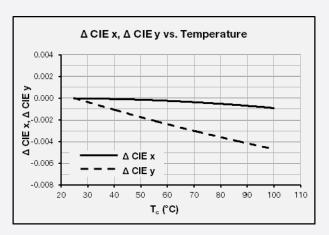


d) Color Shift Characteristics



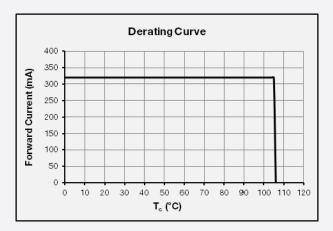




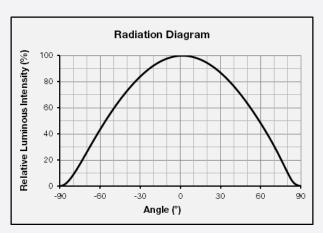




e) Derating Curve

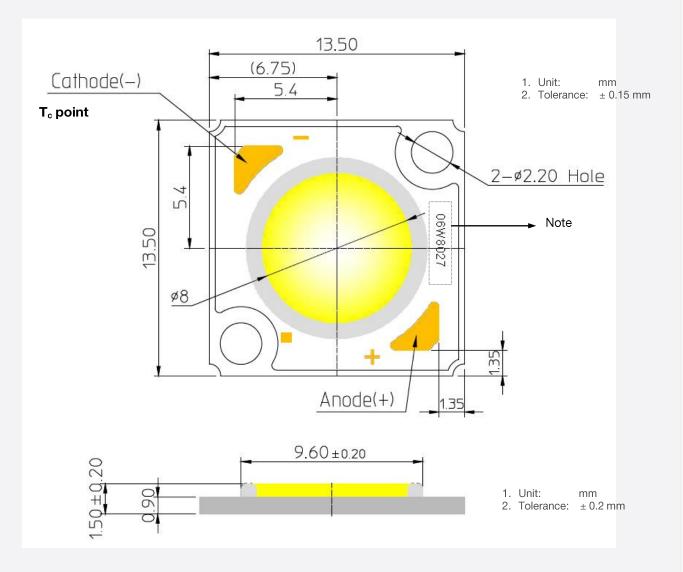


f) Beam Angle Characteristics (I_F = 180 mA, T_c = 25 °C)





4. Outline Drawing & Dimension



ltem	Dimension	Tolerance	Unit
Length	13.50	±0.15	mm
Width	13.50	±0.15	mm
Height	1.50	±0.20	mm
Light Emitting Surface (LES) Diameter	8	±0.15	mm
Screw Hole Size	2.2	±0.15	mm

Note: Denoted product information above is only an example

(06W8027:6.4W, CRI80+, 2700K)



5. Reliability Test Items & Conditions

a) Test Items

Test Item	Test Condition	Test Hour / Cycle
Room Temperature Life Test	25 °C, I _F = max	1000 h
High Temperature Humidity Life Test	60 °C, 90 % RH, DC Derating, I _F = max	1000 h
High Temperature Life Test	105 °C, DC Derating, I _F = max	1000 h
Low Temperature Life Test	-40 °C, DC 320 mA	1000 h
High Temperature Storage	120 °C	1000 h
Low Temperature Storage	-40 °C	1000 h
Thermal Shock	-45 °C / 15 min ↔ 125 °C / 15 min temperature change in 5 min	200 cycles
Temperature Cycle On/Off Test	-40 °C / 85 °C each 20 min, 100 min transfer power on/off each 5 min, DC 180 mA	100 cycles
Temperature Humidity Storage Test	-10 °C ↔ 25 °C, 95 % RH ↔ 85 °C, 95 % RH (24 h / cycle)	100 cycles
ESD (HBM)	R₁: 10 MΩ R₂: 1.5 kΩ C: 100 pF V: ±2 kV	5 times
ESD (MM)	R_{1} : $10M\Omega$ R_{2} : $0k\Omega$ C : $200pF$ V : $\pm 0.5kV$	5 times
Vibration Test	20 ~ 80 Hz (displacement: 0.06 inch, max. 20 g) 80 ~ 2 kHz (max. 20 g) min. frequency ↔ max. frequency 4 min transfer	4 times
Mechanical Shock Test	1500 g, 0.5 ms each of the 6 surfaces (3 axis x 2 sides)	5 times
Salt Spray Test	35 °C, 5 % salt water 8 h spray, 16 h dwell	2 cycles

b) Criteria for Judging the Damage

ltem	Symbol	Test Condition	Lin	Limit	
	Зушоог	(T _c = 25 °C)	Max.		
Forward Voltage	V _F	$I_{\text{F}}=180\;\text{mA}$	L.S.L. * 0.9	U.S.L. * 1.1	
Luminous Flux	$\Phi_{\rm v}$	I _F = 180 mA	L.S.L * 0.7	U.S.L * 1.3	

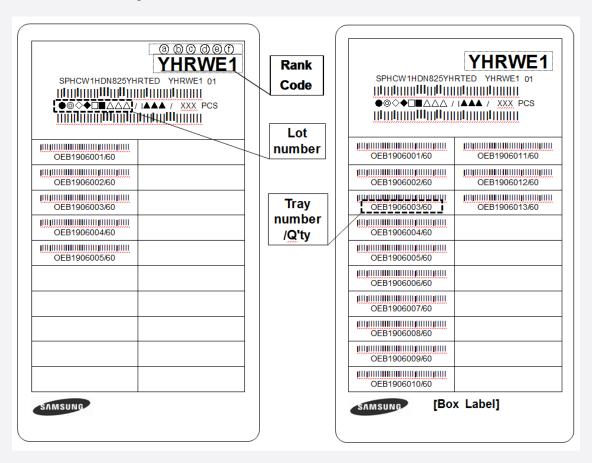


6. Label Structure

a) Label Structure

Aluminum Bag & Inner Box

Outer Box



Note: Denoted rank code and product code above is only an example (see description on page 5)

Rank Code:

(refer to page 6-7)

©d: Chromaticity bin (refer to page 8-9)

(ef): Luminous Flux bin (refer to page 6-7)



b) Lot Number

The lot number is composed of the following characters:

● ◎ ◇ ◆ □ ■ △ △ △ / 1 ▲ ▲ ▲ / xxx PCS

• : Production site (S: Giheung, Korea, G: Tianjin, China)

© : L (LED)

♦ : Product state (A: Normal, B: Bulk, C: First Production, R: Reproduction, S: Sample)

• Year (Y: 2014, Z: 2015, A: 2016, ...)

☐ : Month (1~9, A, B, C)

■ : Day (1~9, A, B~V)

 $\triangle \triangle \triangle$: Product serial number (001 ~ 009)

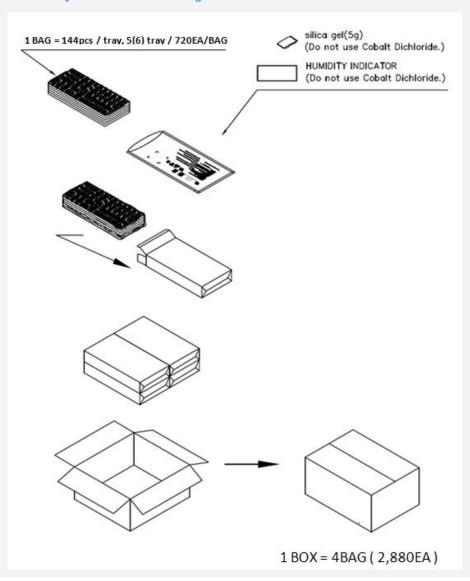
▲ ▲ : Tray number (001 ~ 999)



7. Packing Structure

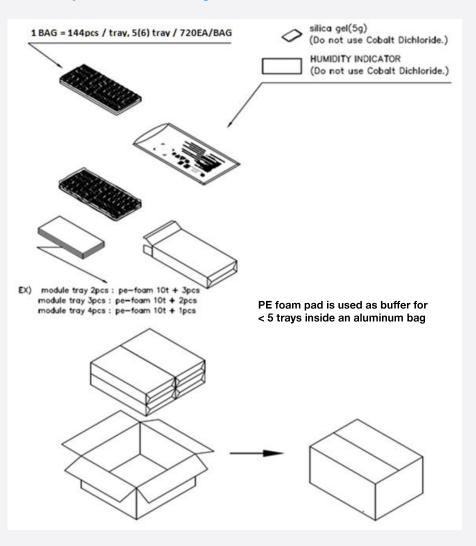
De din a matarial	Max. quantity	Dimension (mm)			
Packing material	in pcs of COB	Length	Width	Height	Tolerance
Tray	144	322.6	135.9	11	0.25
Aluminum Bag	720 (5 trays)	450	230	-	10
PE Foam Pad	-	280	130	10	2
Inner Box	720 (1 aluminum bag)	338	143	55	2
Outer Box	2880 (4 inner boxes)	346	303	120	5
Pallet	161,280 (56 outer boxes)	1000	1000	970	10

a) Packing Structure for 5 trays inside Aluminum Bag

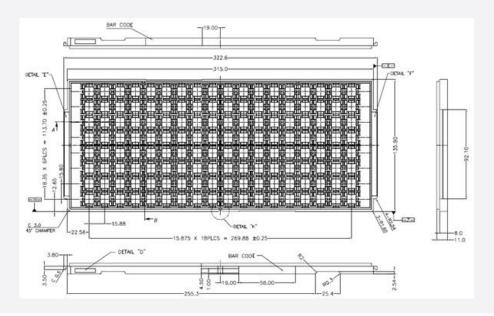




b) Packing Structure for <5 trays inside Aluminum Bag

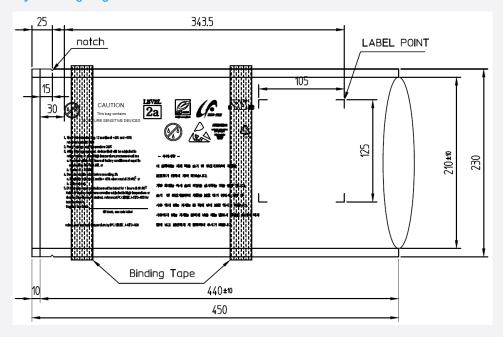


c) Tray





d) Aluminum Vinyl Packing Bag



e) Silica Gel & Humidity Indicator Card inside Aluminum Vinyl Packing Bag

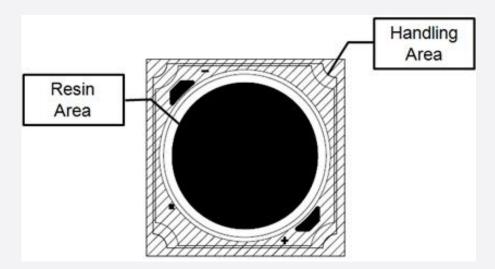






8. Precautions in Handling & Use

- 1) This device should not be used in any type of fluid such as water, oil, organic solvent, etc. When cleaning is required, IPA is recommended as the cleaning agent. Some solvent-based cleaning agent may damage the silicone resins used in the device.
- 2) LEDs must be stored in a clean environment. If the LEDs are to be stored for three months or more after being shipped from Samsung, they should be packed with a nitrogen-filled container (shelf life of sealed bags is 12 months at temperature 0~40 °C, 0~90 % RH).
- 3) After storage bag is opened, device subjected to soldering, solder reflow, or other high temperature processes must be:
 - a. Mounted within 672 hours (28 days) at an assembly line with a condition of no more than 30 °C / 60 % RH, or
 - b. Stored at <10 % RH
- 4) Repack unused products with anti-moisture packing, fold to close any opening and then store in a dry place.
- 5) Devices require baking before mounting, if humidity card reading is >60 % at 23 ± 5 °C.
- 6) Devices must be baked for 1 hour at 60 ± 5 °C, if baking is required.
- 7) The LEDs are sensitive to the static electricity and surge current. It is recommended to use a wrist band or antielectrostatic glove when handling the LEDs. If voltage exceeding the absolute maximum rating is applied to LEDs, it may cause damage or even destruction to LED devices. Damaged LEDs may show some unusual characteristics such as increase in leakage current, lowered turn-on voltage, or abnormal lighting of LEDs at low current.
- 8) VOCs (Volatile Organic Compounds) can be generated from adhesives, flux, hardener or organic additives used in luminaires (fixtures). Transparent LED silicone encapsulant is permeable to those chemicals and they may lead to a discoloration of encapsulant when they exposed to heat or light. This phenomenon can cause a significant loss of light emitted (output) from the luminaires. In order to prevent these problems, we recommend users to know the physical properties of materials used in luminaires and they must be carefully selected.
- 9) The resin area is very sensitive, please do not handle, press, touch, rub, clean, or pick by with tweezers on it. Instead, please pick at the handling area as indicated below.





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